TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOS -H)

TK100E10NE

■ E-Bike/UPS/Inverter

Note: This product is designed for E-Bike / UPS / Inverter in China / India market.

• Low drain–source on-resistance : $R_{DS(ON)} = 4.3 \text{ m}\Omega \text{ (typ.)}$ • Low leakage current : $I_{DSS} = 10 \text{ }\mu\text{A} \text{ (max)} \text{ (V}_{DS} = 100 \text{ V)}$ • Enhancement mode : $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	100	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	100	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	100	Α	
	DC (Note 1,4)	C (Note 1,4) I _D 90		Α	
	Pulse (Note 1)	I _{DP}	670	Α	
Drain power dissipation (Tc = 25°C)		PD	230	W	
Single pulse avalanche energy (Note 2)		E _{AS}	65	mJ	
Avalanche current		I _{AR}	50	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	23	mJ	
Peak diode recovery dv/dt (Note 5)		dv/dt	12	V/ns	
Channel temperature (Note 4)		T _{ch}	175	°C	
Storage temperature range (Note 4)		T _{stg}	-55~175	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th(ch-c)}	0.65	°C/W
Thermal resistance, channel to ambient	R _{th(ch-a)}	83.3	°C/W

Note 1: Ensure that the channel temperature does not exceed 175°C.

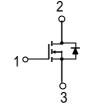
Note 2: V_{DD} = 25 V, T_{Ch} = 25 °C (initial), L = 42 μ H, R_G = 25 Ω , I_{AR} = 50A

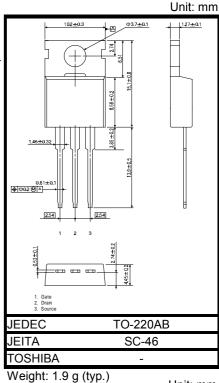
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

Note 4: Tc = 100°C

Note 5: I_{DR} 80 A,di/dt 160 A/ μ s, Tch Tch max., V_{DS} peak < V_{DSS}

This transistor is an electrostatic-sensitive device. Please handle with caution.





Unit: mm

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Weight: 1.9 g (typ.)

Note :Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc). Thermal Characteristics

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Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	irrent	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V	_	_	±0.1	μΑ
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 100 V, V _{DS} = 0 V	_	_	10	μΑ
Drain-source breakdown voltage		V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	100	_	_	V
		V (BR) DSX	I _D = 10 mA, V _{GS} = -20 V(Note 5)	65	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 50 A	_	4.3	5.1	mΩ
Input capacitano	e	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		5590	_	pF
Reverse transfe	r capacitance	C _{rss}			350	_	
Output capacita	nce	Coss			2680	_	
Rise time Turn-on time Fall time Turn-off time	Rise time	t _r	10 V	_	18	_	
	Turn-on time	t _{on}		_	44	_	- ns
	Fall time	t _f		_	27	_	
	Turn-off time	t _{off}	$V_{DD} \approx 50 \text{ V}$ Duty ≤ 1%, $t_W = 10 \text{ μs}$	_	86	_	
Total gate charg plus gate-drain)		Qg			83		
Gate-source charge		Q _{gs}	$V_{DD} \approx 80 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 100 \text{ A}$	_	63	_	nC
Gate-drain ("mil	ler") charge	Q _{gd}			20	_	

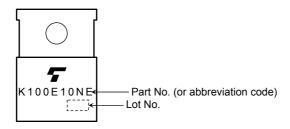
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	100	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	-	-	670	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 100 A, V _{GS} = 0 V		-	-1.5	V
Reverse recovery time(Note 6)	t _{rr}	I _{DR} = 100 A, V _{GS} = 0 V		88		ns
Reverse recovery charge(Note 6)	Q _{rr}	dI _{DR} /dt = 50 A/μs	_	93	_	nC

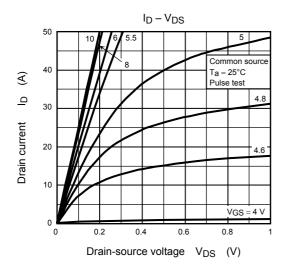
Note 5: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

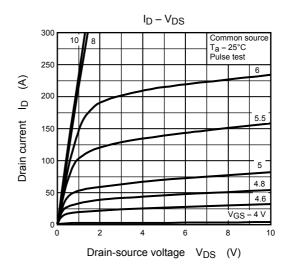
Note 6: Ensure that V_{DS} peak does not exceed V_{DSS} .

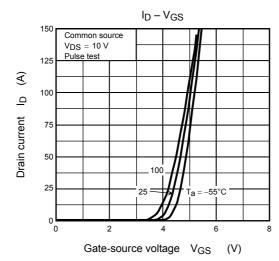
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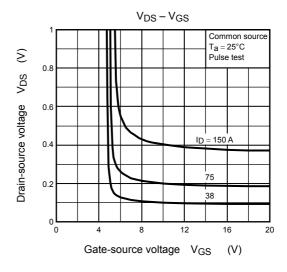


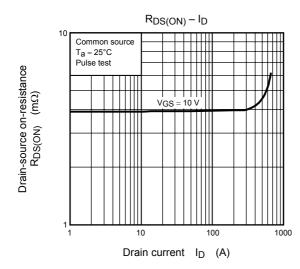
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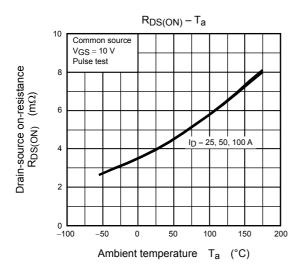


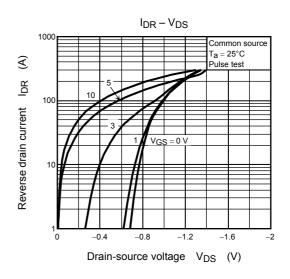


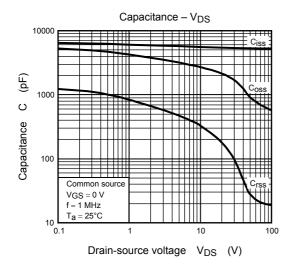


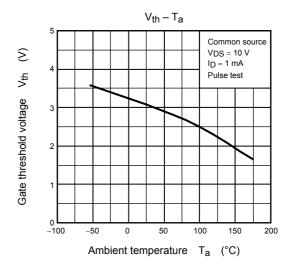


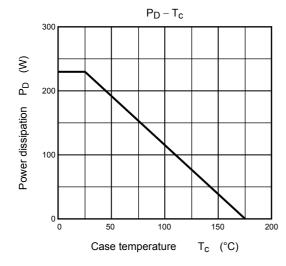


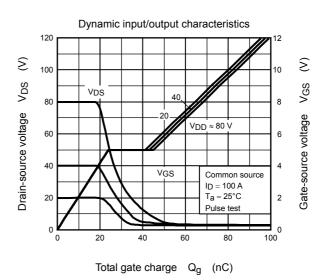






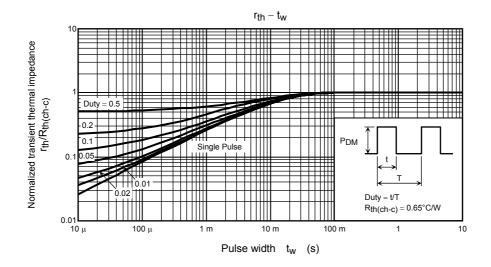


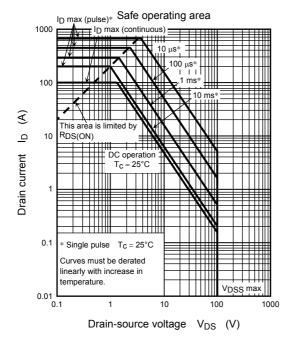


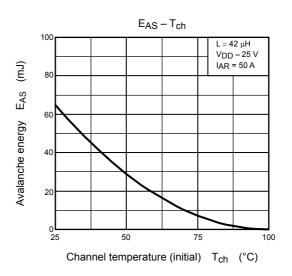


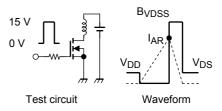
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$$\begin{array}{ll} R_G = 25~\Omega \\ V_{DD} = 25~V,~L = 42~\mu H \end{array} \qquad E_{AS} = \frac{1}{2} \cdot L \cdot I^2_{~AR} \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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